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## **Supplementary Material**

Theoretical Study on the Effects of Alloying Elements on  $TiO_2/Ti_2AlNb$  Interface Adhesion Properties

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This Supplementary Material includes seven Supplementary Figures:

Figure S1. Convergence of cutoff energy and k-mesh

Figure S2.  $W_{sep}$ -distance curve and stress-strain curve of normal separation process of alloying elements doped TiO<sub>2</sub>/Ti<sub>2</sub>AlNb interface

Figure S3.  $W_{sep}$ -distance curve and stress-strain curve of tangential separation process of alloying elements doped TiO<sub>2</sub>/Ti<sub>2</sub>AlNb interface

Figure S4. Differential charge densities of the bare  $TiO_2/Ti_2AlNb$  interface during normal separation

Figure S5. Differential charge densities of the Si element doped (Nb substituted) TiO<sub>2</sub>/Ti<sub>2</sub>AlNb interface during normal separation

Figure S6. Differential charge densities of the Hf element doped (Nb substituted) TiO<sub>2</sub>/Ti<sub>2</sub>AlNb interface during normal separation

Figure S7. The relaxation process of first-principles molecular dynamics Figure S8. Structural changes of the  $TiO_2/Ti_2AINb$  interface at 1100K





Fig. 1 Convergence of cutoff energy and k-mesh



![](_page_2_Figure_0.jpeg)

Fig. 2 a) W<sub>sep</sub>-distance curve and b) stress-strain curve of normal separation process of alloying elements doped (Al substituted) TiO<sub>2</sub>/Ti<sub>2</sub>AlNb interface, c) W<sub>sep</sub>-distance curve and d) stress-strain curve of normal separation process of alloying elements doped (Ti substituted) TiO<sub>2</sub>/Ti<sub>2</sub>AlNb interface, e) W<sub>sep</sub>-distance curve and f) stress-strain curve of normal separation process of alloying elements doped (Nb substituted) TiO<sub>2</sub>/Ti<sub>2</sub>AlNb interface

![](_page_3_Figure_1.jpeg)

![](_page_4_Figure_0.jpeg)

Fig. 3 a)  $W_{sep}$ -distance curve and b) stress-strain curve of tangential separation process of alloying elements doped (Al substituted) TiO<sub>2</sub>/Ti<sub>2</sub>AlNb interface, c)  $W_{sep}$ -distance curve and d) stress-strain curve of tangential separation process of alloying elements doped (Ti substituted) TiO<sub>2</sub>/Ti<sub>2</sub>AlNb interface, e)  $W_{sep}$ -distance curve and f) stressstrain curve of tangential separation process of alloying elements doped (Nb substituted) TiO<sub>2</sub>/Ti<sub>2</sub>AlNb interface

![](_page_5_Figure_0.jpeg)

Fig. 4 Differential charge densities of the bare TiO<sub>2</sub>/Ti<sub>2</sub>AlNb interface during normal separation, a) Strain value of 0%, b) Strain value of 1.46%, c) Strain value of 3.65%, d) Strain value of 7.3%

![](_page_5_Figure_2.jpeg)

Fig. 5 Differential charge densities of the Si element doped (Nb substituted)
TiO<sub>2</sub>/Ti<sub>2</sub>AlNb interface during normal separation, a) Strain value of 0%, b) Strain value of 1.46%, c) Strain value of 3.65%, d) Strain value of 7.3%

![](_page_5_Figure_4.jpeg)

Fig. 6 Differential charge densities of the Hf element doped (Nb substituted)
TiO<sub>2</sub>/Ti<sub>2</sub>AlNb interface during normal separation, a) Strain value of 0%, b) Strain value of 1.46%, c) Strain value of 3.65%, d) Strain value of 7.3%

![](_page_6_Figure_0.jpeg)

![](_page_7_Figure_0.jpeg)

Fig. 7 The relaxation process of first-principles molecular dynamics, a) the bare  $TiO_2/Ti_2AINb$  interface, b) the Si doped  $TiO_2/Ti_2AINb$  interface, c) the Hf doped  $TiO_2/Ti_2AINb$  interface

![](_page_7_Figure_2.jpeg)

Fig. 8 Structural changes of the  $TiO_2/Ti_2AINb$  interface at 1100K, a) the bare TiO\_2/Ti\_2AINb interface, b) the Si doped  $TiO_2/Ti_2AINb$  interface, c) the Hf doped  $TiO_2/Ti_2AINb$  interface